

TQFP, BGA
Commercial Temp
Industrial Temp

256K x 18, 128K x 32, 128K x 36
4Mb Sync Burst SRAMs

190 MHz–100 MHz
3.3 V V_{DD}
3.3 V and 2.5 V I/O

Features

- \overline{FT} pin for user-configurable flow through or pipelined operation
- Dual Cycle Deselect (DCD) operation
- 3.3 V +10%/–5% core power supply
- 2.5 V or 3.3 V I/O supply
- \overline{LBO} pin for Linear or Interleaved Burst mode
- Internal input resistors on mode pins allow floating mode pins
- Default to Interleaved Pipelined mode
- Byte Write (\overline{BW}) and/or Global Write (\overline{GW}) operation
- Common data inputs and data outputs
- Clock control, registered, address, data, and control
- Internal self-timed write cycle
- Automatic power-down for portable applications
- JEDEC standard 100-lead TQFP or 119-Bump BGA package
- Pb-Free 100-lead TQFP package available

Functional Description

Applications

The GS840E18/32/36A is a 4,718,592-bit (4,194,304-bit for x32 version) high performance synchronous SRAM with a 2-bit burst address counter. Although of a type originally developed for Level 2 Cache applications supporting high performance CPUs, the device now finds application in synchronous SRAM applications ranging from DSP main store to networking chip set support. The GS840E18/32/36A is available in a JEDEC standard 100-lead TQFP or 119-Bump BGA package.

Controls

Addresses, data I/Os, chip enables (\overline{E}_1 , \overline{E}_2 , \overline{E}_3), address burst control inputs (\overline{ADSP} , \overline{ADSC} , \overline{ADV}), and write control inputs (\overline{Bx} , \overline{BW} , \overline{GW}) are synchronous and are controlled by a positive-edge-triggered clock input (CK). Output enable (\overline{G}) and power down control (ZZ) are asynchronous inputs. Burst cycles can be initiated with either \overline{ADSP} or \overline{ADSC} inputs. In Burst mode, subsequent burst addresses are generated internally and are controlled by \overline{ADV} . The burst address

counter may be configured to count in either linear or interleave order with the Linear Burst Order (\overline{LBO}) input. The burst function need not be used. New addresses can be loaded on every cycle with no degradation of chip performance.

Flow Through/Pipeline Reads

The function of the Data Output register can be controlled by the user via the \overline{FT} mode pin/bump (pin 14 in the TQFP and bump 5R in the BGA). Holding the \overline{FT} mode pin/bump low places the RAM in Flow Through mode, causing output data to bypass the Data Output Register. Holding \overline{FT} high places the RAM in Pipelined mode, activating the rising-edge-triggered Data Output Register.

DCD Pipelined Reads

The GS840E18/32/36A is a DCD (Dual Cycle Deselect) pipelined synchronous SRAM. SCD (Single Cycle Deselect) versions are also available. DCD SRAMs pipeline disable commands to the same degree as read commands. DCD RAMs hold the deselect command for one full cycle and then begin turning off their outputs just after the second rising edge of clock.

Byte Write and Global Write

Byte write operation is performed by using byte write enable (\overline{BW}) input combined with one or more individual byte write signals (\overline{Bx}). In addition, Global Write (\overline{GW}) is available for writing all bytes at one time, regardless of the Byte Write control inputs.

Sleep Mode

Low power (Sleep mode) is attained through the assertion (High) of the ZZ signal, or by stopping the clock (CK). Memory data is retained during Sleep mode.

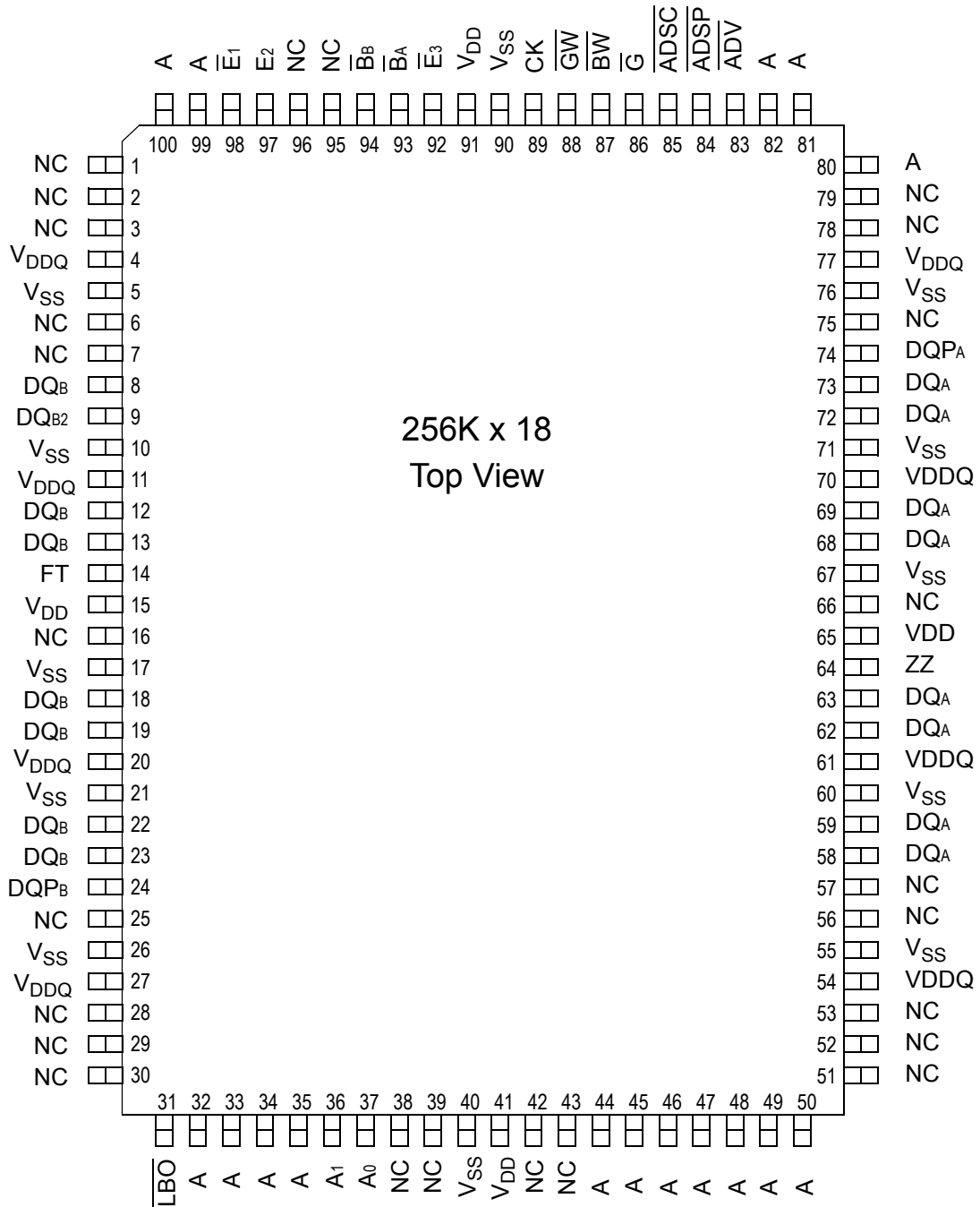
Core and Interface Voltages

The GS840E18/32/36A operates on a 3.3 V power supply and all inputs/outputs are 3.3 V- and 2.5 V-compatible. Separate output power (V_{DDQ}) pins are used to de-couple output noise from the internal circuit.

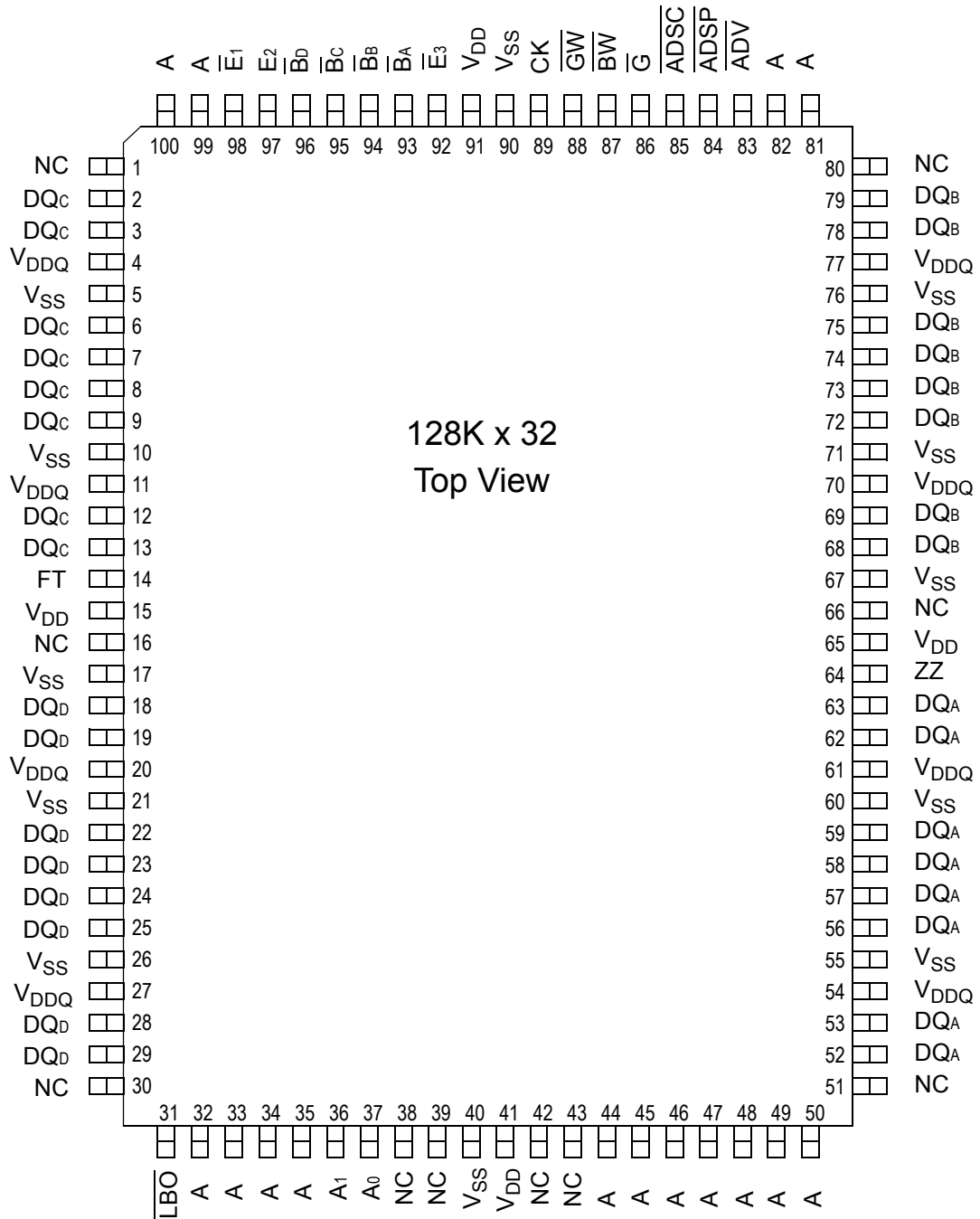
Parameter Synopsis

| | | –190 | –180 | –166 | –150 | –100 |
|----------------------------|-----------------|--------|--------|--------|--------|--------|
| Pipeline 3-1-1-1 | tCycle | 5.3 ns | 5.5 ns | 6.0 ns | 6.6 ns | 10 ns |
| | tkQ | 3.0 ns | 3.0 ns | 3.5 ns | 3.8 ns | 4.5 ns |
| | I _{DD} | 370 mA | 335 mA | 310 mA | 280 mA | 190 mA |
| Flow Through 2-1-1-1 | tkQ | 7.5 ns | 8 ns | 8.5 ns | 10 ns | 12 ns |
| | tCycle | 8.5 ns | 9 ns | 10 ns | 12 ns | 15 ns |
| | I _{DD} | 245 mA | 210 mA | 190 mA | 165 mA | 135 mA |

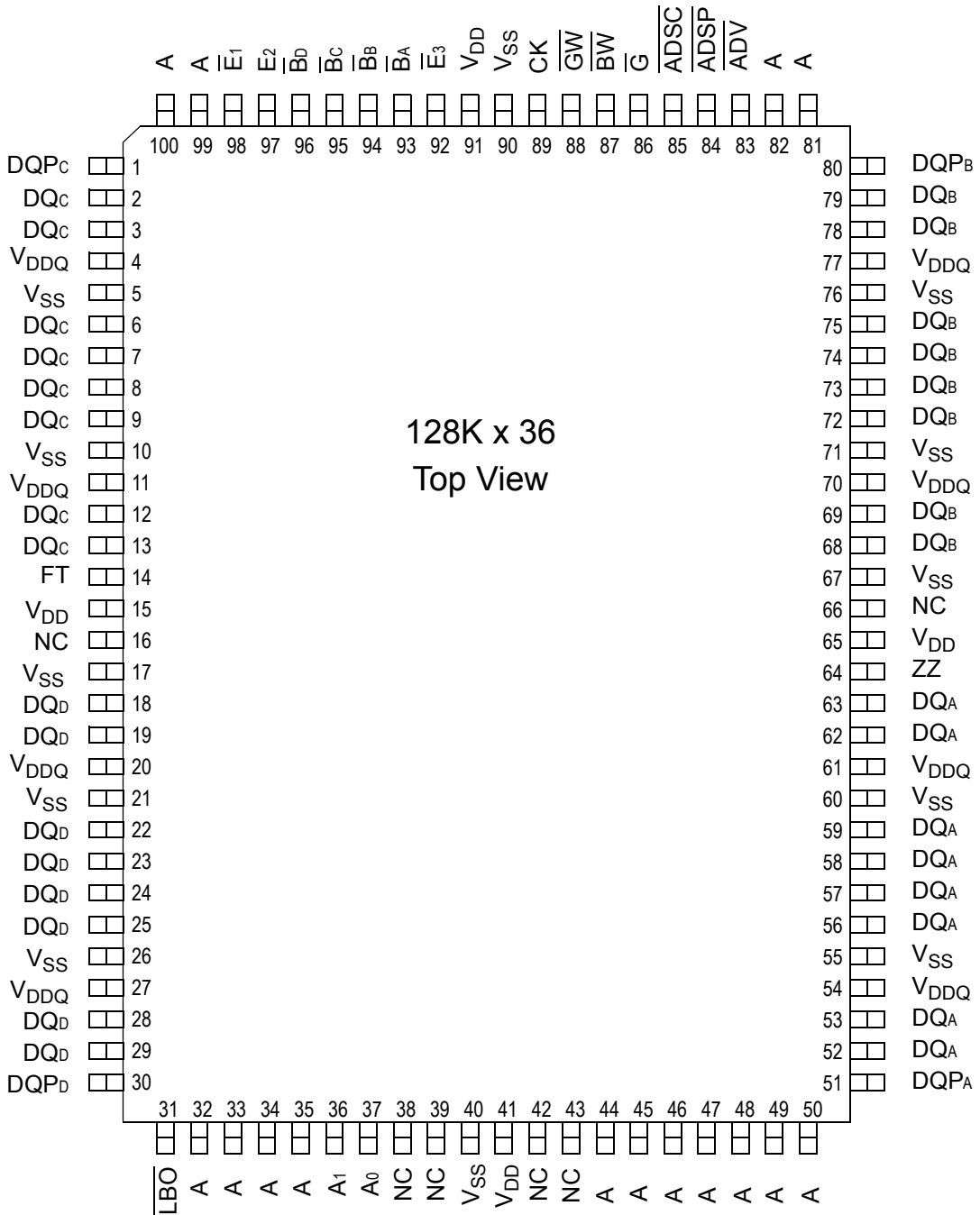
GS840E18A 100-Pin TQFP Pinout (Package T)



GS840E32A 100-Pin TQFP Pinout (Package T)



GS840E36A 100-Pin TQFP Pinout (Package T)



TQFP Pin Description

| Symbol | Type | Description |
|--|-------------|---|
| A ₀ , A ₁ | I | Address field LSBs and Address Counter preset Inputs |
| A | I | Address Inputs |
| DQ _A DQ _B DQ _C DQ _D | I/O | Data Input and Output pins |
| \overline{BW} | I | Byte Write—Writes all enabled bytes; active low |
| \overline{BA} , \overline{BB} | I | Byte Write Enable for DQ _A , DQ _B Data I/s; active low |
| \overline{BC} , \overline{BD} | I | Byte Write Enable for DQ _C , DQ _D Data I/Os; active low |
| CK | I | Clock Input Signal; active high |
| \overline{GW} | I | Global Write Enable—Writes all bytes; active low |
| $\overline{E1}$, $\overline{E3}$ | I | Chip Enable; active low |
| E ₂ | I | Chip Enable; active high |
| \overline{G} | I | Output Enable; active low |
| \overline{ADV} | I | Burst address counter advance enable; active low |
| \overline{ADSP} , \overline{ADSC} | I | Address Strobe (Processor, Cache Controller); active low |
| ZZ | I | Sleep Mode control; active high |
| \overline{FT} | I | Flow Through or Pipeline mode; active low |
| \overline{LBO} | I | Linear Burst Order mode; active low |
| V _{DD} | I | Core power supply |
| V _{SS} | I | I/O and Core Ground |
| V _{DDQ} | I | Output driver power supply |
| NC | - | No Connect |

GS840E18A Pad Out—119-Bump BGA—Top View (Package B)

| | 1 | 2 | 3 | 4 | 5 | 6 | 7 |
|---|------------------|------------------|-------------------------|--------------------------|-------------------------|-------------------------|------------------|
| A | V _{DDQ} | A | A | $\overline{\text{ADSP}}$ | A | A | V _{DDQ} |
| B | NC | E | A | $\overline{\text{ADSC}}$ | A | $\overline{\text{E}}_3$ | NC |
| C | NC | A | A | V _{DD} | A | A | NC |
| D | DQB | NC | V _{SS} | NC | V _{SS} | DQPA | NC |
| E | NC | DQB | V _{SS} | $\overline{\text{E}}_1$ | V _{SS} | NC | DQA |
| F | V _{DDQ} | NC | V _{SS} | $\overline{\text{G}}$ | V _{SS} | DQA | V _{DDQ} |
| G | NC | DQB | $\overline{\text{B}}_B$ | $\overline{\text{ADV}}$ | NC | NC | DQA |
| H | DQB | NC | V _{SS} | $\overline{\text{GW}}$ | V _{SS} | DQA | NC |
| J | V _{DDQ} | V _{DD} | NC | V _{DD} | NC | V _{DD} | V _{DDQ} |
| K | NC | DQB | V _{SS} | CK | V _{SS} | NC | DQA |
| L | DQB | NC | NC | NC | $\overline{\text{B}}_A$ | DQA | NC |
| M | V _{DDQ} | DQB | V _{SS} | $\overline{\text{BW}}$ | V _{SS} | NC | V _{DDQ} |
| N | DQB | NC | V _{SS} | A ₁ | V _{SS} | DQA | NC |
| P | NC | DQP _B | V _{SS} | A ₀ | V _{SS} | NC | DQA |
| R | NC | A | $\overline{\text{LBO}}$ | V _{DD} | $\overline{\text{FT}}$ | A | NC |
| T | NC | A | A | NC | A | A | ZZ |
| U | V _{DDQ} | NC | NC | NC | NC | NC | V _{DDQ} |

GS840E32A Pad Out—119-Bump BGA—Top View (Package B)

| | 1 | 2 | 3 | 4 | 5 | 6 | 7 |
|---|------------------|-----------------|-------------------------|--------------------------|-------------------------|-------------------------|------------------|
| A | V _{DDQ} | A | A | $\overline{\text{ADSP}}$ | A | A | V _{DDQ} |
| B | NC | E | A | $\overline{\text{ADSC}}$ | A | $\overline{\text{E}}_3$ | NC |
| C | NC | A | A | V _{DD} | A | A | NC |
| D | DQc | NC | V _{SS} | NC | V _{SS} | NC | DQB |
| E | DQc | DQc | V _{SS} | $\overline{\text{E}}_1$ | V _{SS} | DQB | DQB |
| F | V _{DDQ} | DQc | V _{SS} | $\overline{\text{G}}$ | V _{SS} | DQB | V _{DDQ} |
| G | DQc | DQc | $\overline{\text{B}}_c$ | $\overline{\text{ADV}}$ | $\overline{\text{B}}_b$ | DQB | DQB |
| H | DQc | DQc | V _{SS} | $\overline{\text{GW}}$ | V _{SS} | DQB | DQB |
| J | V _{DDQ} | V _{DD} | NC | V _{DD} | NC | V _{DD} | V _{DDQ} |
| K | DQd | DQd | V _{SS} | CK | V _{SS} | DQA | DQA |
| L | DQd | DQd | $\overline{\text{B}}_d$ | NC | $\overline{\text{B}}_a$ | DQA | DQA |
| M | V _{DDQ} | DQd | V _{SS} | $\overline{\text{BW}}$ | V _{SS} | DQA | V _{DDQ} |
| N | DQd | DQd | V _{SS} | A ₁ | V _{SS} | DQA | DQA |
| P | DQd | NC | V _{SS} | A ₀ | V _{SS} | NC | DQA |
| R | NC | A | $\overline{\text{LBO}}$ | V _{DD} | $\overline{\text{FT}}$ | A | NC |
| T | NC | NC | A | A | A | NC | ZZ |
| U | V _{DDQ} | NC | NC | NC | NC | NC | V _{DDQ} |

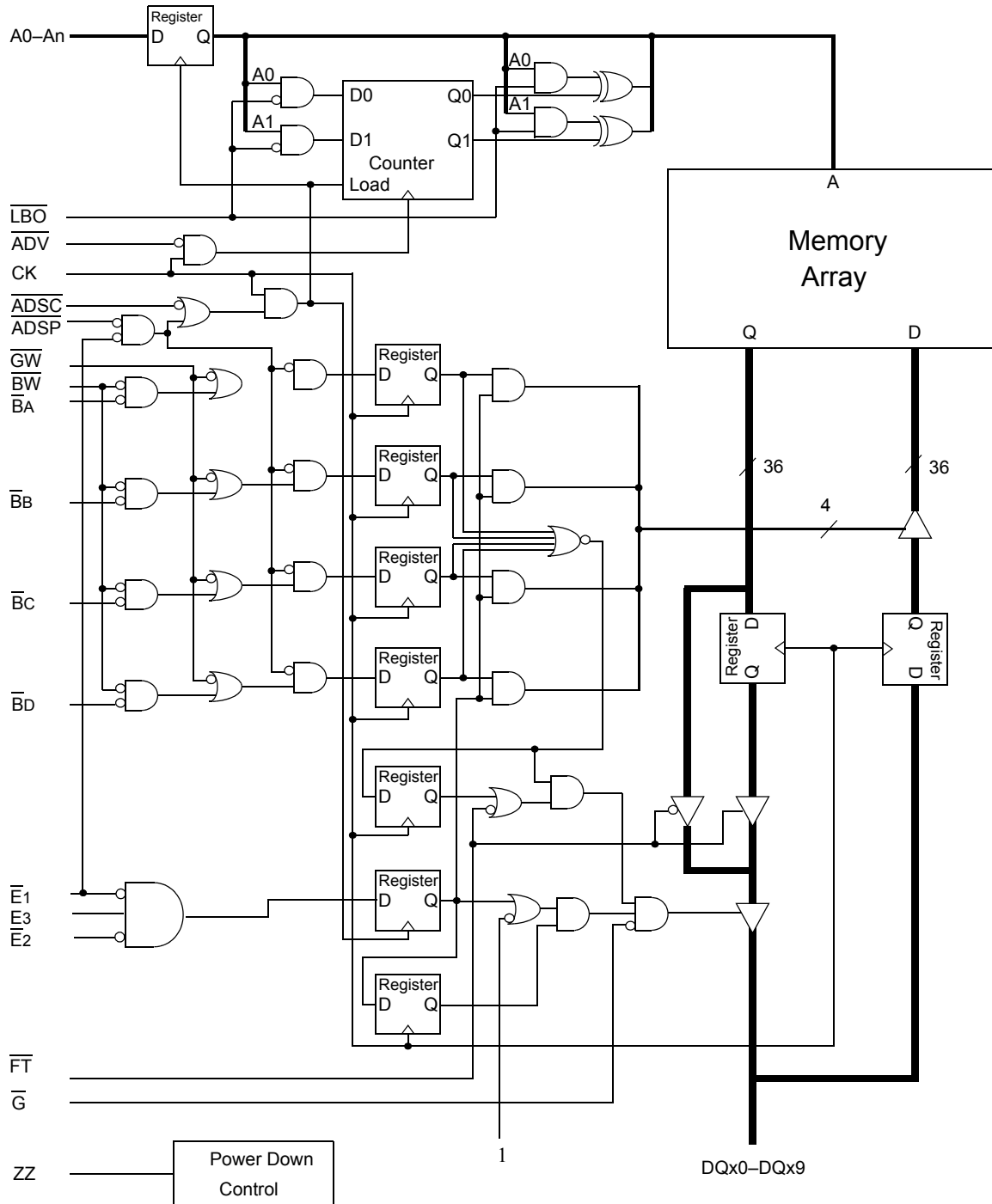
GS840E36APad Out—119-Bump BGA—Top View (Package B)

| | 1 | 2 | 3 | 4 | 5 | 6 | 7 |
|---|------------------|-----------------|-------------------------|--------------------------|-------------------------|-------------------------|------------------|
| A | V _{DDQ} | A | A | $\overline{\text{ADSP}}$ | A | A | V _{DDQ} |
| B | NC | E | A | $\overline{\text{ADSC}}$ | A | $\overline{\text{E}}_3$ | NC |
| C | NC | A | A | V _{DD} | A | A | NC |
| D | DQc | DQPc | V _{SS} | NC | V _{SS} | DQPb | DQb |
| E | DQc | DQc | V _{SS} | $\overline{\text{E}}_1$ | V _{SS} | DQb | DQb |
| F | V _{DDQ} | DQc | V _{SS} | $\overline{\text{G}}$ | V _{SS} | DQb | V _{DDQ} |
| G | DQc | DQc | $\overline{\text{B}}_c$ | $\overline{\text{ADV}}$ | $\overline{\text{B}}_b$ | DQb | DQb |
| H | DQc | DQc | V _{SS} | $\overline{\text{GW}}$ | V _{SS} | DQb | DQb |
| J | V _{DDQ} | V _{DD} | NC | V _{DD} | NC | V _{DD} | V _{DDQ} |
| K | DQd | DQd | V _{SS} | CK | V _{SS} | DQA | DQA |
| L | DQd | DQd | $\overline{\text{B}}_d$ | NC | $\overline{\text{B}}_a$ | DQA | DQA |
| M | V _{DDQ} | DQd | V _{SS} | $\overline{\text{BW}}$ | V _{SS} | DQA | V _{DDQ} |
| N | DQd | DQd | V _{SS} | A ₁ | V _{SS} | DQA | DQA |
| P | DQd | DQPd | V _{SS} | A ₀ | V _{SS} | DQPA | DQA |
| R | NC | A | $\overline{\text{LBO}}$ | V _{DD} | $\overline{\text{FT}}$ | A | NC |
| T | NC | NC | A | A | A | NC | ZZ |
| U | V _{DDQ} | NC | NC | NC | NC | NC | V _{DDQ} |

BGA Pin Description

| Symbol | Type | Description |
|---|-------------|---|
| A ₀ , A ₁ | I | Address field LSBs and Address Counter Preset Inputs |
| A | I | Address Inputs |
| DQA DQB DQC DQD | I/O | Data Input and Output pins |
| \overline{BA} , \overline{BB} , \overline{BC} , \overline{BD} | I | Byte Write Enable for DQA, DQB, DQC, DQD I/Os; active low |
| CK | I | Clock Input Signal; active high |
| \overline{BW} | I | Byte Write—Writes all enabled bytes; active low |
| \overline{GW} | I | Global Write Enable—Writes all bytes; active low |
| \overline{E}_1 , \overline{E}_3 | I | Chip Enable; active low |
| E ₂ | I | Chip Enable; active high |
| \overline{G} | I | Output Enable; active low |
| \overline{ADV} | I | Burst address counter advance enable; active low |
| \overline{ADSP} , \overline{ADSC} | I | Address Strobe (Processor, Cache Controller); active low |
| ZZ | I | Sleep Mode control; active high |
| \overline{FT} | I | Flow Through or Pipeline mode; active low |
| \overline{LBO} | I | Linear Burst Order mode; active low |
| V _{DD} | I | Core power supply |
| V _{SS} | I | I/O and Core Ground |
| V _{DDQ} | I | Output driver power supply |
| NC | — | No Connect |

GS840E18/32/36A Block Diagram



Note: Only x36 version shown for simplicity.

Mode Pin Functions

| Mode Name | Pin Name | State | Function |
|-------------------------|-------------------------|---------|----------------------------|
| Burst Order Control | $\overline{\text{LBO}}$ | L | Linear Burst |
| | | H or NC | Interleaved Burst |
| Output Register Control | $\overline{\text{FT}}$ | L | Flow Through |
| | | H or NC | Pipeline |
| Power Down Control | ZZ | L or NC | Active |
| | | H | Standby, $I_{DD} = I_{SB}$ |

Note:

There are pull-up devices on $\overline{\text{LBO}}$ and $\overline{\text{FT}}$ pins and a pull down device on the ZZ pin, so those input pins can be unconnected and the chip will operate in the default states as specified in the above tables.

Burst Counter Sequences
Linear Burst Sequence

| | A[1:0] | A[1:0] | A[1:0] | A[1:0] |
|-------------|--------|--------|--------|--------|
| 1st address | 00 | 01 | 10 | 11 |
| 2nd address | 01 | 10 | 11 | 00 |
| 3rd address | 10 | 11 | 00 | 01 |
| 4th address | 11 | 00 | 01 | 10 |

Note:

The burst counter wraps to initial state on the 5th clock.

Interleaved Burst Sequence

| | A[1:0] | A[1:0] | A[1:0] | A[1:0] |
|-------------|--------|--------|--------|--------|
| 1st address | 00 | 01 | 10 | 11 |
| 2nd address | 01 | 00 | 11 | 10 |
| 3rd address | 10 | 11 | 00 | 01 |
| 4th address | 11 | 10 | 01 | 00 |

Note:

The burst counter wraps to initial state on the 5th clock.

Byte Write Truth Table

| Function | \overline{GW} | \overline{BW} | $\overline{B_A}$ | $\overline{B_B}$ | $\overline{B_C}$ | $\overline{B_D}$ | Notes |
|-----------------|-----------------|-----------------|------------------|------------------|------------------|------------------|---------|
| Read | H | H | X | X | X | X | 1 |
| Read | H | L | H | H | H | H | 1 |
| Write byte A | H | L | L | H | H | H | 2, 3 |
| Write byte B | H | L | H | L | H | H | 2, 3 |
| Write byte c | H | L | H | H | L | H | 2, 3, 4 |
| Write byte D | H | L | H | H | H | L | 2, 3, 4 |
| Write all bytes | H | L | L | L | L | L | 2, 3, 4 |
| Write all bytes | L | X | X | X | X | X | |

Notes:

1. All byte outputs are active in read cycles regardless of the state of Byte Write Enable inputs.
2. Byte Write Enable inputs $\overline{B_A}$, $\overline{B_B}$, $\overline{B_C}$ and/or $\overline{B_D}$ may be used in any combination with \overline{BW} to write single or multiple bytes.
3. All byte I/Os remain High-Z during all write operations regardless of the state of Byte Write Enable inputs.
4. Bytes "c" and "d" are only available on the x32 and x36 versions.

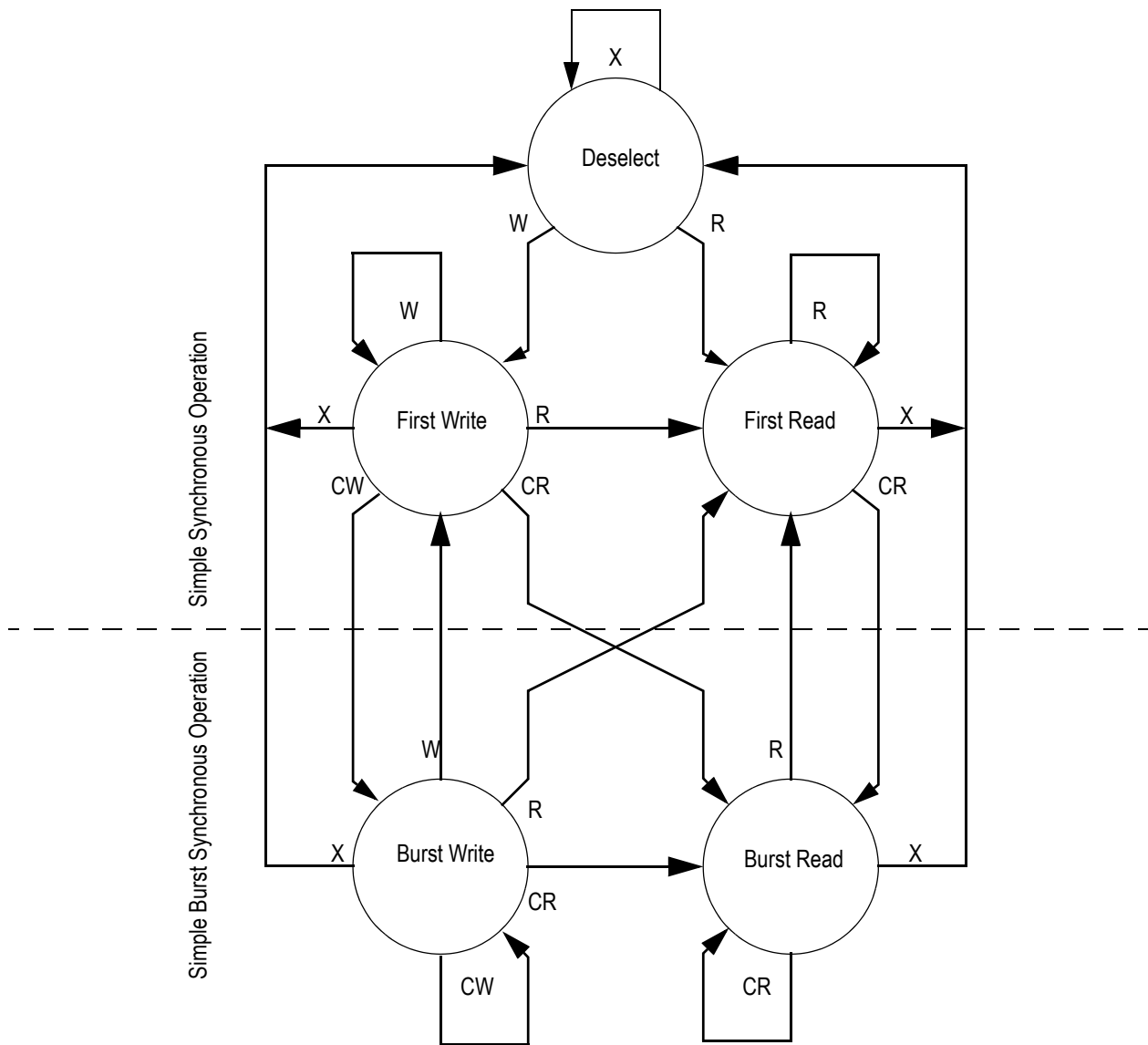
Synchronous Truth Table

| Operation | Address Used | State Diagram Key ⁵ | \bar{E}_1 | E^2 | \overline{ADSP} | \overline{ADSC} | \overline{ADV} | W^3 | DQ^4 |
|------------------------------------|-----------------|--------------------------------|-------------|----------|-------------------|-------------------|------------------|----------|---------------|
| Deselect Cycle, Power Down | None | X | H | X | X | L | X | X | High-Z |
| Deselect Cycle, Power Down | None | X | L | F | L | X | X | X | High-Z |
| Deselect Cycle, Power Down | None | X | L | F | H | L | X | X | High-Z |
| Read Cycle, Begin Burst | External | R | L | T | L | X | X | X | Q |
| Read Cycle, Begin Burst | External | R | L | T | H | L | X | F | Q |
| Write Cycle, Begin Burst | External | W | L | T | H | L | X | T | D |
| <i>Read Cycle, Continue Burst</i> | <i>Next</i> | <i>CR</i> | <i>X</i> | <i>X</i> | <i>H</i> | <i>H</i> | <i>L</i> | <i>F</i> | <i>Q</i> |
| Read Cycle, Continue Burst | Next | CR | H | X | X | H | L | F | Q |
| <i>Write Cycle, Continue Burst</i> | <i>Next</i> | <i>CW</i> | <i>X</i> | <i>X</i> | <i>H</i> | <i>H</i> | <i>L</i> | <i>T</i> | <i>D</i> |
| Write Cycle, Continue Burst | Next | CW | H | X | X | H | L | T | D |
| Read Cycle, Suspend Burst | Current | | X | X | H | H | H | F | Q |
| Read Cycle, Suspend Burst | Current | | H | X | X | H | H | F | Q |
| Write Cycle, Suspend Burst | Current | | X | X | H | H | H | T | D |
| Write Cycle, Suspend Burst | Current | | H | X | X | H | H | T | D |

Notes:

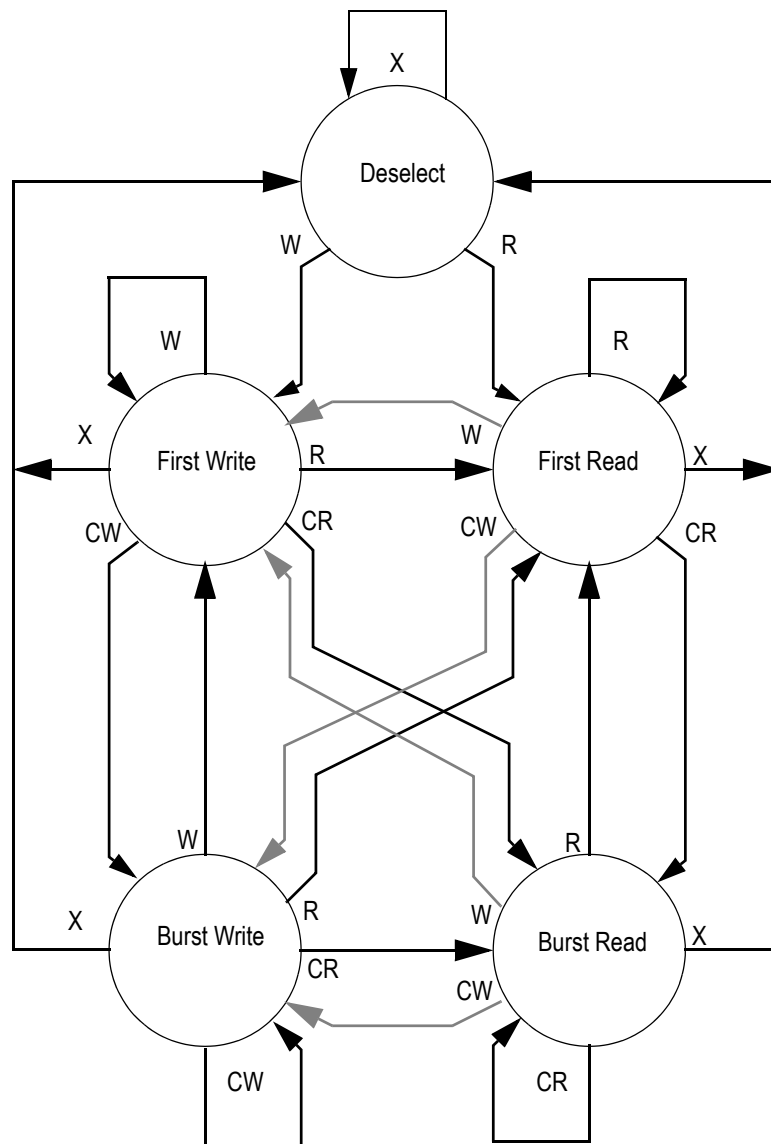
1. X = Don't Care, H = High, L = Low.
2. E = T (True) if $E_2 = 1$ and $\bar{E}_3 = 0$; E = F (False) if $E_2 = 0$ or $\bar{E}_3 = 1$.
3. W = T (True) and F (False) is defined in the Byte Write Truth Table preceding.
4. \bar{G} is an asynchronous input. \bar{G} can be driven high at any time to disable active output drivers. \bar{G} low can only enable active drivers (shown as "Q" in the Truth Table above).
5. All input combinations shown above are tested and supported. Input combinations shown in gray boxes need not be used to accomplish basic synchronous or synchronous burst operations and may be avoided for simplicity.
6. Tying \overline{ADSP} high and \overline{ADSC} low allows simple non-burst synchronous operations. See **BOLD** items above.
7. Tying \overline{ADSP} high and \overline{ADV} low while using \overline{ADSC} to load new addresses allows simple burst operations. See *ITALIC* items above.

Simplified State Diagram



Notes:

1. The diagram shows only supported (tested) synchronous state transitions. The diagram presumes \overline{G} is tied Low.
2. The upper portion of the diagram assumes active use of only the Enable ($\overline{E}_1, E_2, \overline{E}_3$) and Write ($\overline{B}_A, \overline{B}_B, \overline{B}_C, \overline{B}_D, \overline{B}_W$ and \overline{G}_W) control inputs and that \overline{ADSP} is tied high and \overline{ADSC} is tied low.
3. The upper and lower portions of the diagram together assume active use of only the Enable, Write and \overline{ADSC} control inputs and assumes \overline{ADSP} is tied high and \overline{ADV} is tied low.

Simplified State Diagram with \overline{G}

Notes:

1. The diagram shows supported (tested) synchronous state transitions plus supported transitions that depend upon the use of \overline{G} .
2. Use of "Dummy Reads" (Read Cycles with \overline{G} High) may be used to make the transition from Read cycles to Write cycles without passing through a Deselect cycle. Dummy Read cycles increment the address counter just like normal Read cycles.
3. Transitions shown in grey tone assume \overline{G} has been pulsed high long enough to turn the RAM's drivers off and for incoming data to meet Data Input Set Up Time.

Absolute Maximum Ratings

 (All voltages reference to V_{SS})

| Symbol | Description | Value | Unit |
|------------|-------------------------------|--|-------------|
| V_{DD} | Voltage on V_{DD} Pins | -0.5 to 4.6 | V |
| V_{DDQ} | Voltage in V_{DDQ} Pins | -0.5 to V_{DD} | V |
| V_{CK} | Voltage on Clock Input Pin | -0.5 to 6 | V |
| $V_{I/O}$ | Voltage on I/O Pins | -0.5 to $V_{DDQ} + 0.5$ (≤ 4.6 V max.) | V |
| V_{IN} | Voltage on Other Input Pins | -0.5 to $V_{DD} + 0.5$ (≤ 4.6 V max.) | V |
| I_{IN} | Input Current on Any Pin | +/-20 | mA |
| I_{OUT} | Output Current on Any I/O Pin | +/-20 | mA |
| P_D | Package Power Dissipation | 1.5 | W |
| T_{STG} | Storage Temperature | -55 to 125 | $^{\circ}C$ |
| T_{BIAS} | Temperature Under Bias | -55 to 125 | $^{\circ}C$ |

Note:

Permanent damage to the device may occur if the Absolute Maximum Ratings are exceeded. Operation should be restricted to Recommended Operating Conditions. Exposure to conditions exceeding the Absolute Maximum Ratings, for an extended period of time, may affect reliability of this component.

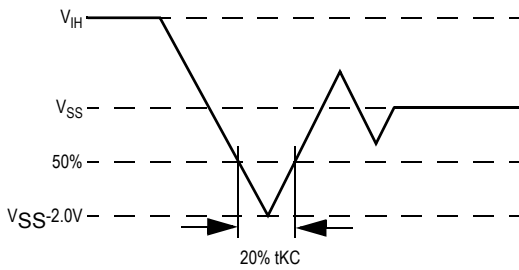
Recommended Operating Conditions

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Notes |
|---|-----------|-------|------|----------------|-------------|-------|
| Supply Voltage | V_{DD} | 3.135 | 3.3 | 3.6 | V | |
| I/O Supply Voltage | V_{DDQ} | 2.375 | 2.5 | V_{DD} | V | 1 |
| Input High Voltage | V_{IH} | 1.7 | — | $V_{DD} + 0.3$ | V | 2 |
| Input Low Voltage | V_{IL} | -0.3 | — | 0.8 | V | 2 |
| Ambient Temperature (Commercial Range Versions) | T_A | 0 | 25 | 70 | $^{\circ}C$ | 3 |
| Ambient Temperature (Industrial Range Versions) | T_A | -40 | 25 | 85 | $^{\circ}C$ | 3 |

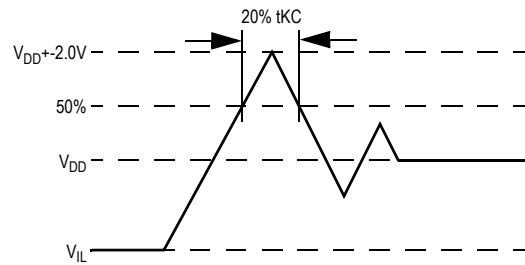
Notes:

- Unless otherwise noted, all performance specifications quoted are evaluated for worst case at both $2.75\text{ V} \leq V_{DDQ} \leq 2.375\text{ V}$ (i.e., 2.5 V I/O) and $3.6\text{ V} \leq V_{DDQ} \leq 3.135\text{ V}$ (i.e., 3.3 V I/O) and quoted at whichever condition is worst case.
- This device features input buffers compatible with both 3.3 V and 2.5 V I/O drivers.
- Most speed grades and configurations of this device are offered in both Commercial and Industrial Temperature ranges. The part number of Industrial Temperature Range versions end the character "I". Unless otherwise noted, all performance specifications quoted are evaluated for worst case in the temperature range marked on the device.
- Input Under/overshoot voltage must be $-2\text{ V} > V_i < V_{DD} + 2\text{ V}$ with a pulse width not to exceed 20% tKC.

Undershoot Measurement and Timing



Overshoot Measurement and Timing



Capacitance

($T_A = 25^\circ\text{C}$, $f = 1 \text{ MHz}$, $V_{DD} = 3.3 \text{ V}$)

| Parameter | Symbol | Test conditions | Typ. | Max. | Unit |
|---------------------------|-----------|--------------------------|------|------|------|
| Control Input Capacitance | C_I | $V_{DD} = 3.3 \text{ V}$ | 3 | 4 | pF |
| Input Capacitance | C_{IN} | $V_{IN} = 0 \text{ V}$ | 4 | 5 | pF |
| Output Capacitance | C_{OUT} | $V_{OUT} = 0 \text{ V}$ | 6 | 7 | pF |

Note:

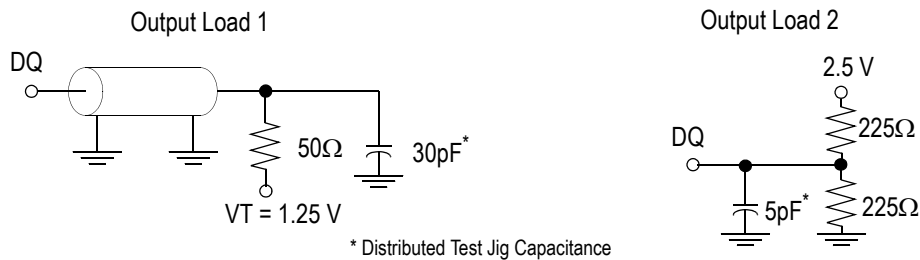
This parameter is sample tested.

AC Test Conditions

| Parameter | Conditions |
|------------------------|-----------------------|
| Input high level | 2.3 V |
| Input low level | 0.2 V |
| Input slew rate | 1 V/ns |
| Input reference level | 1.25 V |
| Output reference level | 1.25 V |
| Output load | Fig. 1 & 2 |

Notes:

1. Include scope and jig capacitance.
2. Test conditions as specified with output loading as shown in **Fig. 1** unless otherwise noted.
3. Output Load 2 for t_{LZ} , t_{HZ} , t_{OLZ} and t_{OHZ} .
4. Device is deselected as defined by the Truth Table.


DC Electrical Characteristics

| Parameter | Symbol | Test Conditions | Min | Max |
|--|------------|--|----------------------------|--------------------------|
| Input Leakage Current (except mode pins) | I_{IL} | $V_{IN} = 0$ to V_{DD} | -1 μ A | 1 μ A |
| ZZ Input Current | I_{INZZ} | $V_{DD} \geq V_{IN} \geq V_{IH}$ $0V \leq V_{IN} \leq V_{IH}$ | -1 μ A -1 μ A | 1 μ A 300 μ A |
| Mode Pin Input Current | I_{INM} | $V_{DD} \geq V_{IN} \geq V_{IL}$ $0V \leq V_{IN} \leq V_{IL}$ | -300 μ A -1 μ A | 1 μ A 1 μ A |
| Output Leakage Current | I_{OL} | Output Disable, $V_{OUT} = 0$ to V_{DD} | -1 μ A | 1 μ A |
| Output High Voltage | V_{OH} | $I_{OH} = -4$ mA, $V_{DDQ} = 2.375$ V | 1.7 V | |
| Output High Voltage | V_{OH} | $I_{OH} = -4$ mA, $V_{DDQ} = 3.135$ V | 2.4 V | |
| Output Low Voltage | V_{OL} | $I_{OL} = 4$ mA | | 0.4 V |

Operating Currents

| Parameter | Test Conditions | Symbol | -190 | | -180 | | -166 | | -150 | | -100 | | Unit |
|-------------------|--|------------------|-----------|-------------|-----------|-------------|-----------|-------------|-----------|-------------|-----------|-------------|------|
| | | | 0 to 70°C | -40 to 85°C | 0 to 70°C | -40 to 85°C | 0 to 70°C | -40 to 85°C | 0 to 70°C | -40 to 85°C | 0 to 70°C | -40 to 85°C | |
| Operating Current | Device Selected; All other inputs $\geq V_{IH}$ or $\leq V_{IL}$ Output open | IDD Pipeline | 370 | 380 | 335 | 345 | 310 | 320 | 280 | 290 | 190 | 200 | mA |
| | | IDD Flow Through | 245 | 255 | 210 | 220 | 190 | 200 | 165 | 175 | 135 | 145 | mA |
| Standby Current | ZZ $\geq V_{DD} - 0.2$ V | ISB Pipeline | 20 | 30 | 20 | 30 | 20 | 30 | 20 | 30 | 20 | 30 | mA |
| | | ISB Flow Through | 20 | 30 | 20 | 30 | 20 | 30 | 20 | 30 | 20 | 30 | mA |
| Deselect Current | Device Deselected; All other inputs $\geq V_{IH}$ or $\leq V_{IL}$ | IDD Pipeline | 60 | 70 | 55 | 65 | 50 | 60 | 50 | 60 | 40 | 50 | mA |
| | | IDD Flow Through | 45 | 55 | 40 | 50 | 40 | 50 | 35 | 45 | 35 | 45 | mA |

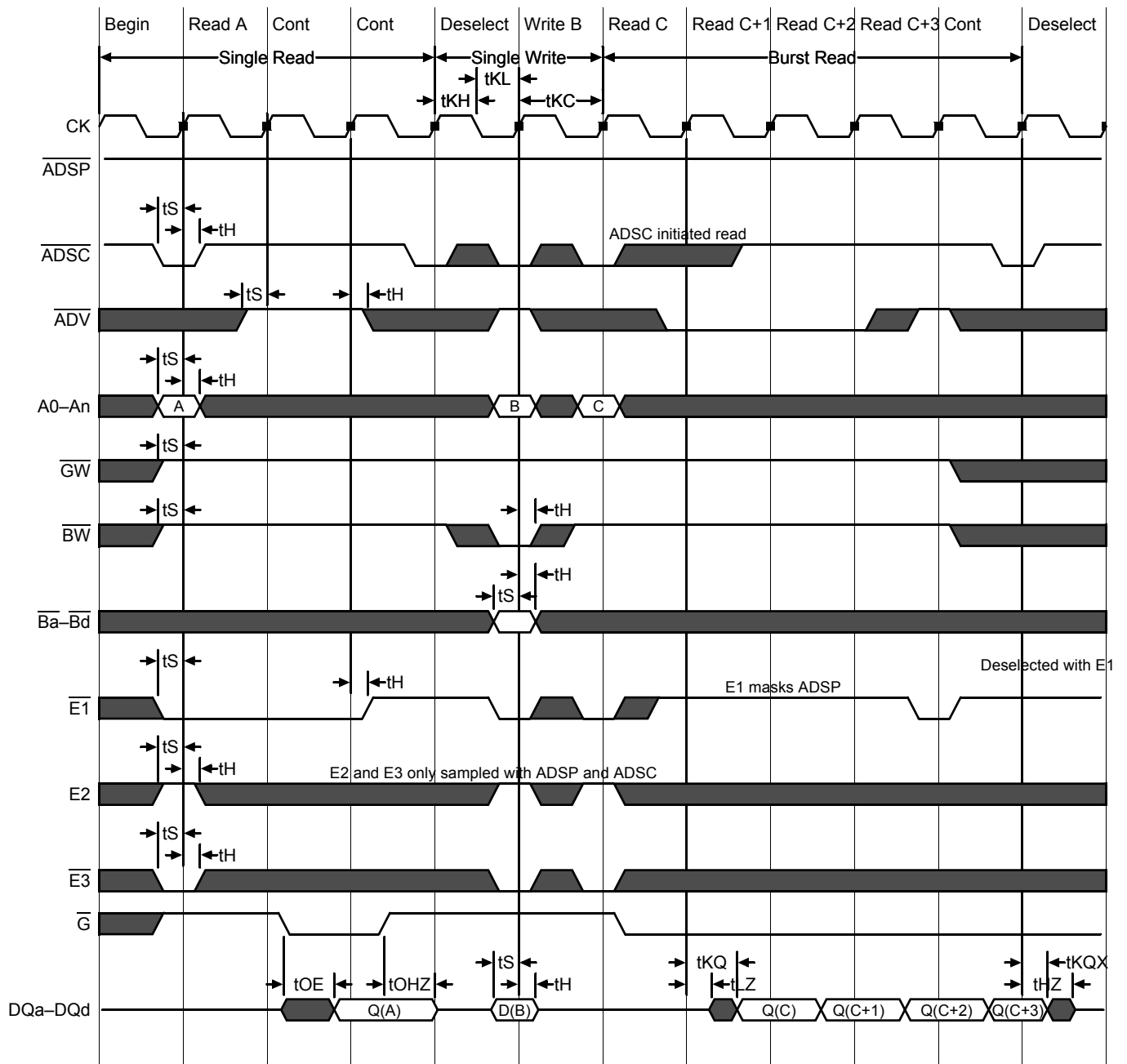
AC Electrical Characteristics

| | Parameter | Symbol | -190 | | -180 | | -166 | | -150 | | -100 | | Unit |
|---------------------|-------------------------------|-------------------------------|------|-----|------|-----|------|-----|------------|------|------|------|------|
| | | | Min | Max | Min | Max | Min | Max | Min | Max | Min | Max | |
| Pipeline | Clock Cycle Time | t _{KC} | 5.3 | — | 5.5 | — | 6.0 | — | 6.7 | — | 10 | — | ns |
| | Clock to Output Valid | t _{KQ} | — | 3.0 | — | 3.0 | — | 3.5 | — | 3.8 | — | 4.5 | ns |
| | Clock to Output Invalid | t _{KQX} | 1.5 | — | 1.5 | — | 1.5 | — | 1.5 | — | 1.5 | — | ns |
| | Clock to Output in Low-Z | t _{LZ} ¹ | 1.5 | — | 1.5 | — | 1.5 | — | 1.5 | — | 1.5 | — | ns |
| Flow Through | Clock Cycle Time | t _{KC} | 8.5 | — | 9.0 | — | 10.0 | — | 12.0 | — | 15.0 | — | ns |
| | Clock to Output Valid | t _{KQ} | — | 7.5 | — | 8.0 | — | 8.5 | — | 10.0 | — | 12.0 | ns |
| | Clock to Output Invalid | t _{KQX} | 3.0 | — | 3.0 | — | 3.0 | — | 3.0 | — | 3.0 | — | ns |
| | Clock to Output in Low-Z | t _{LZ} ¹ | 3.0 | — | 3.0 | — | 3.0 | — | 3.0 | — | 3.0 | — | ns |
| | Clock HIGH Time | t _{KH} | 1.3 | — | 1.3 | — | 1.3 | — | 1.3 | — | 1.3 | — | ns |
| | Clock LOW Time | t _{KL} | 1.5 | — | 1.5 | — | 1.5 | — | 1.5 | — | 1.5 | — | ns |
| | Clock to Output in High-Z | t _{HZ} ¹ | 1.5 | 3.0 | 1.5 | 3.2 | 1.5 | 3.5 | 1.5 | 3.8 | 1.5 | 5 | ns |
| | \bar{G} to Output Valid | t _{OE} | — | 3.0 | — | 3.2 | — | 3.5 | — | 3.8 | — | 5 | ns |
| | \bar{G} to output in Low-Z | t _{OLZ} ¹ | 0 | — | 0 | — | 0 | — | 0 | — | 0 | — | ns |
| | \bar{G} to output in High-Z | t _{OHZ} ¹ | — | 3.0 | — | 3.2 | — | 3.5 | — | 3.8 | — | 5 | ns |
| | Setup time | t _S | 1.5 | — | 1.5 | — | 1.5 | — | 1.5 | — | 2.0 | — | ns |
| | Hold time | t _H | 0.5 | — | 0.5 | — | 0.5 | — | 0.5 | — | 0.5 | — | ns |
| | ZZ setup time | t _{ZZS} ² | 5 | — | 5 | — | 5 | — | 5 | — | 5 | — | ns |
| | ZZ hold time | t _{ZZH} ² | 1 | — | 1 | — | 1 | — | 1 | — | 1 | — | ns |
| | ZZ recovery | t _{ZZR} | 20 | — | 20 | — | 20 | — | 20 | — | 20 | — | ns |

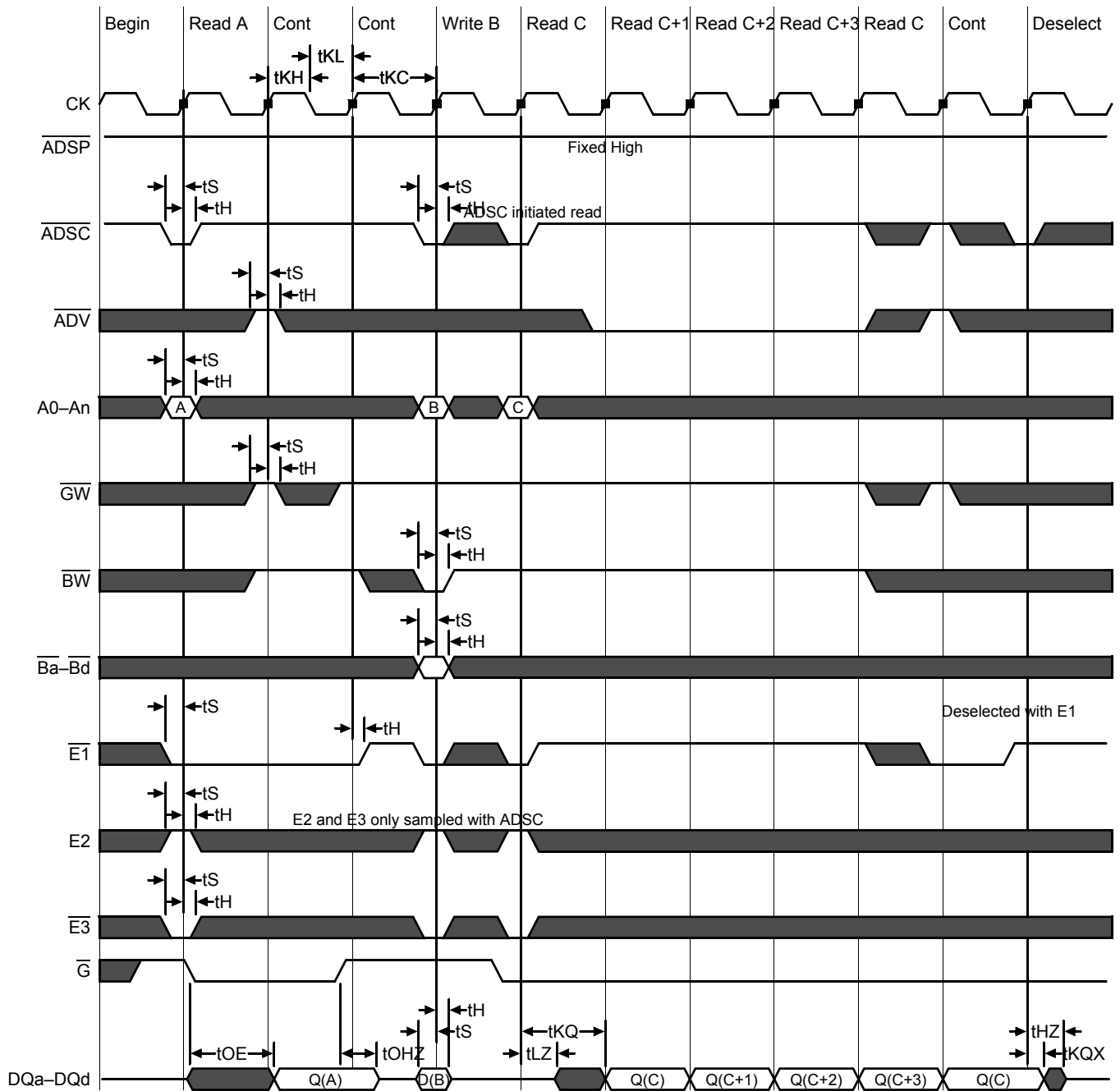
Notes:

1. These parameters are sampled and are not 100% tested
2. ZZ is an asynchronous signal. However, In order to be recognized on any given clock cycle, ZZ must meet the specified setup and hold times as specified above.

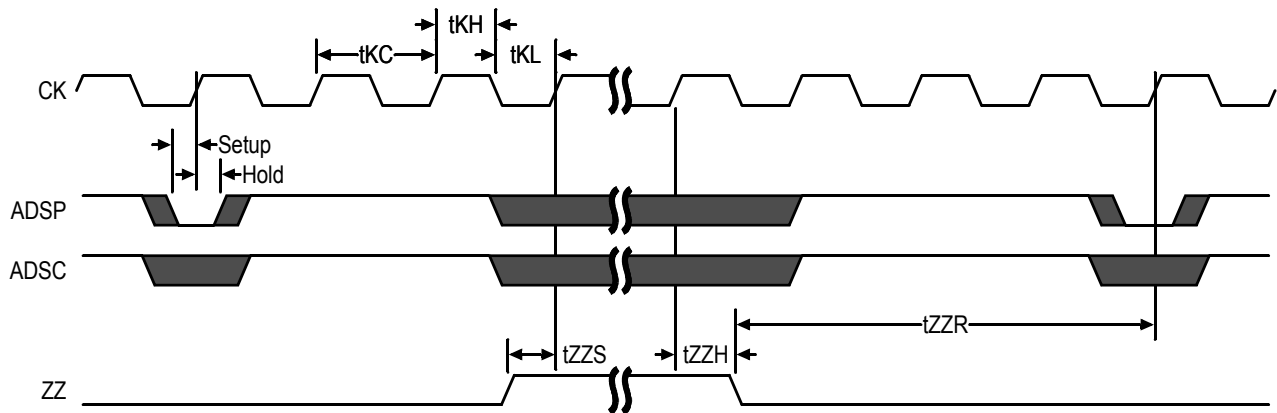
Pipeline Mode Timing



Flow Through Mode Timing



Sleep Mode Timing Diagram

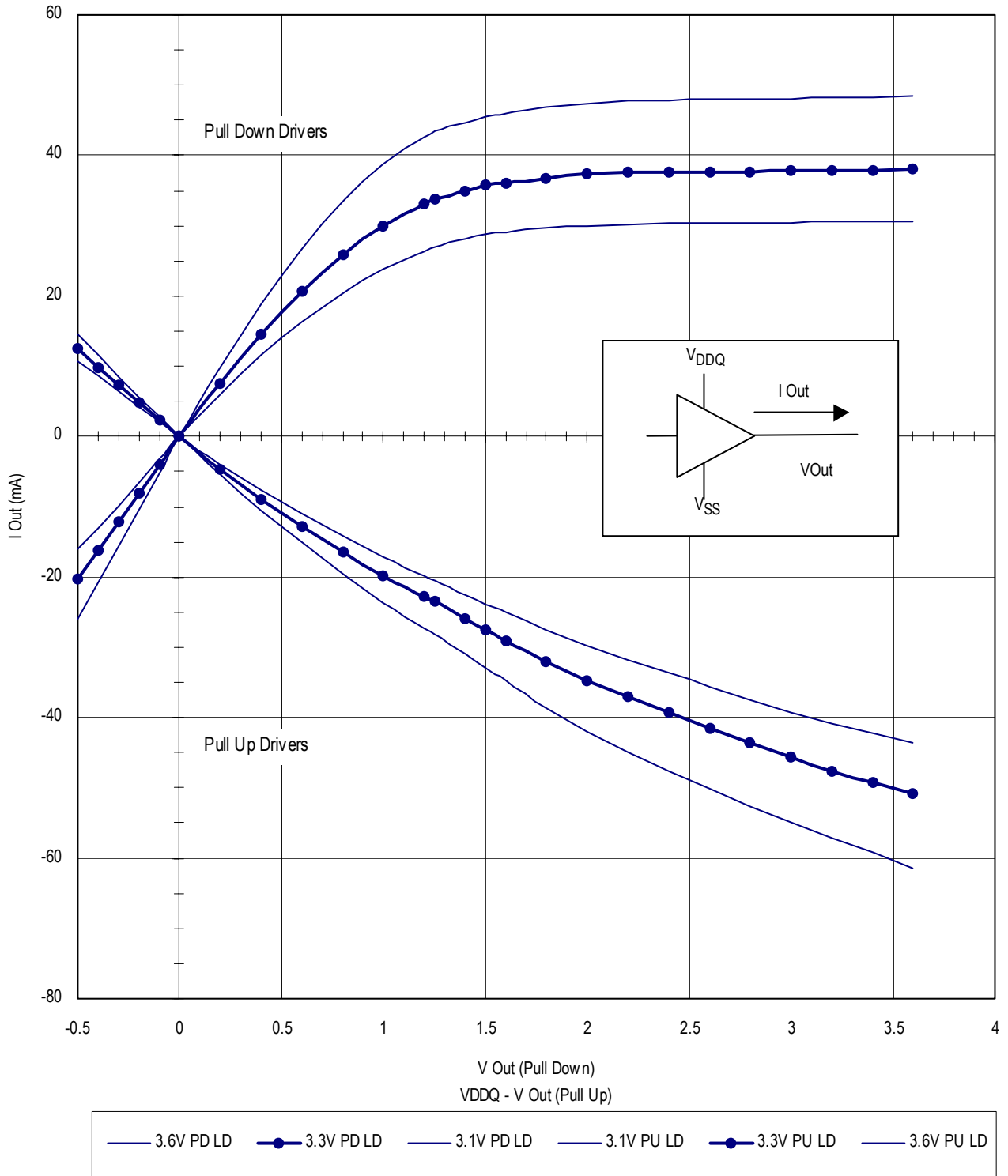


Application Tips

Single and Dual Cycle Deselect

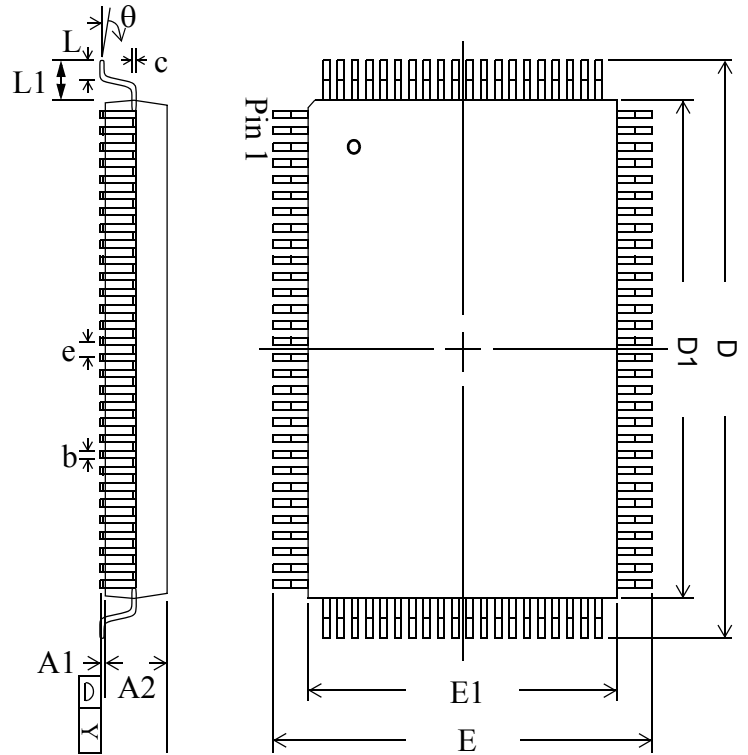
SCD devices force the use of “dummy read cycles” (read cycles that are launched normally but that are ended with the output drivers inactive) in a fully synchronous environment. Dummy read cycles waste performance but their use usually assures there will be no bus contention in transitions from reads to writes or between banks of RAMs. DCD SRAMs do not waste bandwidth on dummy cycles and are logically simpler to manage in a multiple bank application (wait states need not be inserted at bank address boundary crossings), but greater care must be exercised to avoid excessive bus contention.

GS840E18/32/36A Output Driver Characteristics



TQFP Package Drawing (Package T)

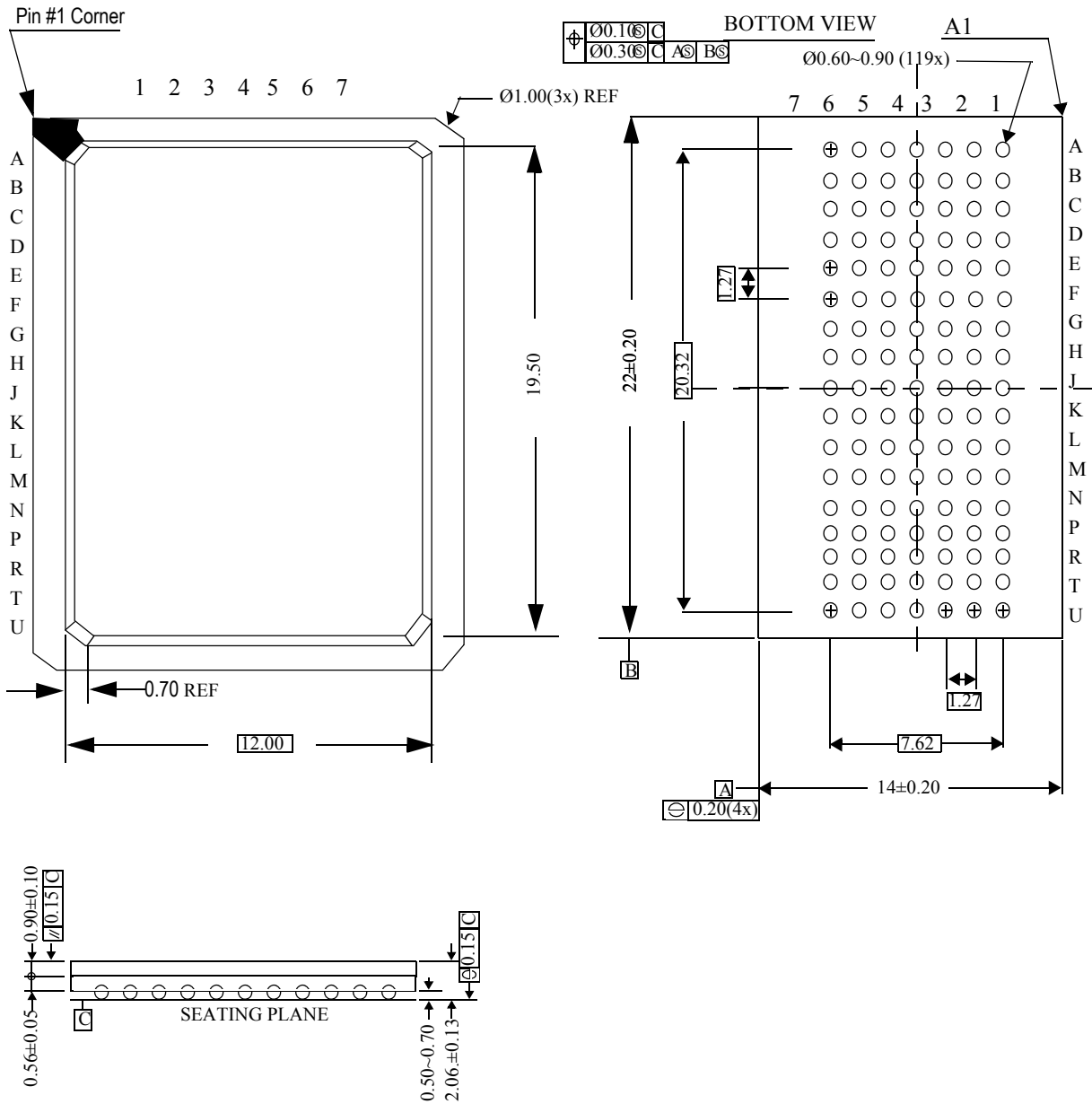
| Symbol | Description | Min. | Nom. | Max |
|----------|--------------------|------|------|------|
| A1 | Standoff | 0.05 | 0.10 | 0.15 |
| A2 | Body Thickness | 1.35 | 1.40 | 1.45 |
| b | Lead Width | 0.20 | 0.30 | 0.40 |
| c | Lead Thickness | 0.09 | — | 0.20 |
| D | Terminal Dimension | 21.9 | 22.0 | 22.1 |
| D1 | Package Body | 19.9 | 20.0 | 20.1 |
| E | Terminal Dimension | 15.9 | 16.0 | 16.1 |
| E1 | Package Body | 13.9 | 14.0 | 14.1 |
| e | Lead Pitch | — | 0.65 | — |
| L | Foot Length | 0.45 | 0.60 | 0.75 |
| L1 | Lead Length | — | 1.00 | — |
| Y | Coplanarity | | | 0.10 |
| θ | Lead Angle | 0° | — | 7° |



Notes:

1. All dimensions are in millimeters (mm).
2. Package width and length do not include mold protrusion.

Package Dimensions—119-Bump FPBGA (Package B, Variation 1)



Ordering Information for GSI Synchronous Burst RAMS

| Org | Part Number ¹ | Type | Package | Speed ² (MHz/ns) | T _A ³ | Status |
|-----------|--------------------------|---------------------------|---------|--------------------------------|-----------------------------|--------|
| 256K x 18 | GS840E18AT-190 | DCD Pipeline/Flow Through | TQFP | 190/7.5 | C | |
| 256K x 18 | GS840E18AT-180 | DCD Pipeline/Flow Through | TQFP | 180/8 | C | |
| 256K x 18 | GS840E18AT-166 | DCD Pipeline/Flow Through | TQFP | 166/8.5 | C | |
| 256K x 18 | GS840E18AT-150 | DCD Pipeline/Flow Through | TQFP | 150/10 | C | |
| 256K x 18 | GS840E18AT-100 | DCD Pipeline/Flow Through | TQFP | 100/12 | C | |
| 128K x 32 | GS840E32AT-190 | DCD Pipeline/Flow Through | TQFP | 190/7.5 | C | |
| 128K x 32 | GS840E32AT-180 | DCD Pipeline/Flow Through | TQFP | 180/8 | C | |
| 128K x 32 | GS840E32AT-166 | DCD Pipeline/Flow Through | TQFP | 166/8.5 | C | |
| 128K x 32 | GS840E32AT-150 | DCD Pipeline/Flow Through | TQFP | 150/10 | C | |
| 128K x 32 | GS840E32AT-100 | DCD Pipeline/Flow Through | TQFP | 100/12 | C | |
| 128K x 36 | GS840E36AT-190 | DCD Pipeline/Flow Through | TQFP | 190/7.5 | C | |
| 128K x 36 | GS840E36AT-180 | DCD Pipeline/Flow Through | TQFP | 180/8 | C | |
| 128K x 36 | GS840E36AT-166 | DCD Pipeline/Flow Through | TQFP | 166/8.5 | C | |
| 128K x 36 | GS840E36AT-150 | DCD Pipeline/Flow Through | TQFP | 150/10 | C | |
| 128K x 36 | GS840E36AT-100 | DCD Pipeline/Flow Through | TQFP | 100/12 | C | |
| 256K x 18 | GS840E18AT-190I | DCD Pipeline/Flow Through | TQFP | 190/7.5 | I | |
| 256K x 18 | GS840E18AT-180I | DCD Pipeline/Flow Through | TQFP | 180/8 | I | |
| 256K x 18 | GS840E18AT-166I | DCD Pipeline/Flow Through | TQFP | 166/8.5 | I | |
| 256K x 18 | GS840E18AT-150I | DCD Pipeline/Flow Through | TQFP | 150/10 | C | |
| 256K x 18 | GS840E18AT-100I | DCD Pipeline/Flow Through | TQFP | 100/12 | C | |
| 128K x 32 | GS840E32AT-190I | DCD Pipeline/Flow Through | TQFP | 190/7.5 | I | |
| 128K x 32 | GS840E32AT-180I | DCD Pipeline/Flow Through | TQFP | 180/8 | I | |
| 128K x 32 | GS840E32AT-166I | DCD Pipeline/Flow Through | TQFP | 166/8.5 | I | |
| 128K x 32 | GS840E32AT-150I | DCD Pipeline/Flow Through | TQFP | 150/10 | C | |
| 128K x 32 | GS840E32AT-100I | DCD Pipeline/Flow Through | TQFP | 100/12 | C | |
| 128K x 36 | GS840E36AT-190I | DCD Pipeline/Flow Through | TQFP | 190/7.5 | I | |
| 128K x 36 | GS840E36AT-180I | DCD Pipeline/Flow Through | TQFP | 180/8 | I | |
| 128K x 36 | GS840E36AT-166I | DCD Pipeline/Flow Through | TQFP | 166/8.5 | I | |
| 128K x 36 | GS840E36AT-150I | DCD Pipeline/Flow Through | TQFP | 150/10 | C | |
| 128K x 36 | GS840E36AT-100I | DCD Pipeline/Flow Through | TQFP | 100/12 | C | |

Notes:

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- The speed column indicates the cycle frequency (MHz) of the device in Pipelined mode and the latency (ns) in Flow Through mode. Each device is Pipeline/Flow through mode-selectable by the user.
- T_A = C = Commercial Temperature Range. T_A = I = Industrial Temperature Range.
- GSI offers other versions this type of device in many different configurations and with a variety of different features, only some of which are covered in this data sheet. See the GSI Technology web site (www.gsitechnology.com) for a complete listing of current offerings.

Ordering Information for GSI Synchronous Burst RAMS (Continued)

| Org | Part Number ¹ | Type | Package | Speed ² (MHz/ns) | T _A ³ | Status |
|-----------|--------------------------|---------------------------|------------------|--------------------------------|-----------------------------|--------|
| 256K x 18 | GS840E18AGT-190 | DCD Pipeline/Flow Through | Pb-free TQFP | 190/7.5 | C | |
| 256K x 18 | GS840E18AGT-180 | DCD Pipeline/Flow Through | Pb-free TQFP | 180/8 | C | |
| 256K x 18 | GS840E18AGT-166 | DCD Pipeline/Flow Through | Pb-free TQFP | 166/8.5 | C | |
| 256K x 18 | GS840E18AGT-150 | DCD Pipeline/Flow Through | Pb-free TQFP | 150/10 | C | |
| 256K x 18 | GS840E18AGT-100 | DCD Pipeline/Flow Through | Pb-free TQFP | 100/12 | C | |
| 128K x 32 | GS840E32AGT-190 | DCD Pipeline/Flow Through | Pb-free TQFP | 190/7.5 | C | |
| 128K x 32 | GS840E32AGT-180 | DCD Pipeline/Flow Through | Pb-free TQFP | 180/8 | C | |
| 128K x 32 | GS840E32AGT-166 | DCD Pipeline/Flow Through | Pb-free TQFP | 166/8.5 | C | |
| 128K x 32 | GS840E32AGT-150 | DCD Pipeline/Flow Through | Pb-free TQFP | 150/10 | C | |
| 128K x 32 | GS840E32AGT-100 | DCD Pipeline/Flow Through | Pb-free TQFP | 100/12 | C | |
| 128K x 36 | GS840E36AGT-190 | DCD Pipeline/Flow Through | Pb-free TQFP | 190/7.5 | C | |
| 128K x 36 | GS840E36AGT-180 | DCD Pipeline/Flow Through | Pb-free TQFP | 180/8 | C | |
| 128K x 36 | GS840E36AGT-166 | DCD Pipeline/Flow Through | Pb-free TQFP | 166/8.5 | C | |
| 128K x 36 | GS840E36AGT-150 | DCD Pipeline/Flow Through | Pb-free TQFP | 150/10 | C | |
| 128K x 36 | GS840E36AGT-100 | DCD Pipeline/Flow Through | Pb-free TQFP | 100/12 | C | |
| 256K x 18 | GS840E18AGT-190I | DCD Pipeline/Flow Through | Pb-free TQFP | 190/7.5 | I | |
| 256K x 18 | GS840E18AGT-180I | DCD Pipeline/Flow Through | Pb-free TQFP | 180/8 | I | |
| 256K x 18 | GS840E18AGT-166I | DCD Pipeline/Flow Through | Pb-free TQFP | 166/8.5 | I | |
| 256K x 18 | GS840E18AGT-150I | DCD Pipeline/Flow Through | Pb-free TQFP | 150/10 | C | |
| 256K x 18 | GS840E18AGT-100I | DCD Pipeline/Flow Through | Pb-free TQFP | 100/12 | C | |
| 128K x 32 | GS840E32AGT-190I | DCD Pipeline/Flow Through | Pb-free TQFP | 190/7.5 | I | |
| 128K x 32 | GS840E32AGT-180I | DCD Pipeline/Flow Through | Pb-free TQFP | 180/8 | I | |
| 128K x 32 | GS840E32AGT-166I | DCD Pipeline/Flow Through | Pb-free TQFP | 166/8.5 | I | |
| 128K x 32 | GS840E32AGT-150I | DCD Pipeline/Flow Through | Pb-free TQFP | 150/10 | C | |
| 128K x 32 | GS840E32AGT-100I | DCD Pipeline/Flow Through | Pb-free TQFP | 100/12 | C | |
| 128K x 36 | GS840E36AGT-190I | DCD Pipeline/Flow Through | Pb-free TQFP | 190/7.5 | I | |
| 128K x 36 | GS840E36AGT-180I | DCD Pipeline/Flow Through | Pb-free TQFP | 180/8 | I | |
| 128K x 36 | GS840E36AGT-166I | DCD Pipeline/Flow Through | Pb-free TQFP | 166/8.5 | I | |
| 128K x 36 | GS840E36AGT-150I | DCD Pipeline/Flow Through | Pb-free TQFP | 150/10 | C | |
| 128K x 36 | GS840E36AGT-100I | DCD Pipeline/Flow Through | Pb-free TQFP | 100/12 | C | |
| 256K x 18 | GS840E18AB-190 | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 190/7.5 | C | |

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- The speed column indicates the cycle frequency (MHz) of the device in Pipelined mode and the latency (ns) in Flow Through mode. Each device is Pipeline/Flow through mode-selectable by the user.
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Ordering Information for GSI Synchronous Burst RAMS (Continued)

| Org | Part Number ¹ | Type | Package | Speed ² (MHz/ns) | T _A ³ | Status |
|-----------|--------------------------|---------------------------|------------------|--------------------------------|-----------------------------|--------|
| 256K x 18 | GS840E18AB-180 | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 180/8 | C | |
| 256K x 18 | GS840E18AB-166 | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 166/8.5 | C | |
| 256K x 18 | GS840E18AB-150 | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 150/10 | C | |
| 256K x 18 | GS840E18AB-100 | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 100/12 | C | |
| 128K x 32 | GS840E32AB-190 | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 190/7.5 | C | |
| 128K x 32 | GS840E32AB-180 | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 180/8 | C | |
| 128K x 32 | GS840E32AB-166 | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 166/8.5 | C | |
| 128K x 32 | GS840E32AB-150 | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 150/10 | C | |
| 128K x 32 | GS840E32AB-100 | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 100/12 | C | |
| 128K x 36 | GS840E36AB-190 | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 190/7.5 | C | |
| 128K x 36 | GS840E36AB-180 | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 180/8 | C | |
| 128K x 36 | GS840E36AB-166 | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 166/8.5 | C | |
| 128K x 36 | GS840E36AB-150 | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 150/10 | C | |
| 128K x 36 | GS840E36AB-100 | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 100/12 | C | |
| 256K x 18 | GS840E18AB-190I | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 190/7.5 | I | |
| 256K x 18 | GS840E18AB-180I | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 180/8 | I | |
| 256K x 18 | GS840E18AB-166I | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 166/8.5 | I | |
| 256K x 18 | GS840E18AB-150I | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 150/10 | C | |
| 256K x 18 | GS840E18AB-100I | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 100/12 | C | |
| 128K x 32 | GS840E32AB-190I | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 190/7.5 | I | |
| 128K x 32 | GS840E32AB-180I | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 180/8 | I | |
| 128K x 32 | GS840E32AB-166I | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 166/8.5 | I | |
| 128K x 32 | GS840E32AB-150I | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 150/10 | C | |
| 128K x 32 | GS840E32AB-100I | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 100/12 | C | |
| 128K x 36 | GS840E36AB-190I | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 190/7.5 | I | |
| 128K x 36 | GS840E36AB-180I | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 180/8 | I | |
| 128K x 36 | GS840E36AB-166I | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 166/8.5 | I | |
| 128K x 36 | GS840E36AB-150I | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 150/10 | C | |
| 128K x 36 | GS840E36AB-100I | DCD Pipeline/Flow Through | 119 BGA (var. 1) | 100/12 | C | |

Notes:

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4Mb Burst SRAM Revision History

| Rev. Code: Old; New | Types of Changes Format or Content | Page /Revisions;Reason |
|---|---|--|
| GS840E18/32/36 Rev 1.02c 5/ 1999; GS840E18/32/36 2.00 8/1999D | Format/Typos | • Document/Continued changing to new format. |
| | Content | • Added Fine Pitch BGA Package. |
| GS840E18/32/362.00 8/ 1999;GS840E18/32/362.01 9/ 1999E | Format/Typos | <ul style="list-style-type: none"> • Took “E” out of 840HE...in Core and Interface Voltages. • Pin outs/New small caps format. • Timing Diagrams/New format. • Block Diagrams/New small caps format. |
| | Content | <ul style="list-style-type: none"> • Pin outs/x32 & x36 TQFP/Changed pin 72 from DQA3 to DQB3. • Pin Description/Rearranged Address Inputs to match order on TQFP Pinout. • TQFP Package Diagram/Corrected Dimension D Max from 20.1 to 22.1. |
| GS840E18/32/362.01 9/ 1999E;GS840E18/32/362.02 | | • Took out Fine Pitch BGA Package. Package change in progress. |
| GS840E18/32/362.0210-11/ 1999;GS840E18/32/362.032/ 2000G | Format | <ul style="list-style-type: none"> • New GSI Logo • Took “Pin” out of heading for consistency. |
| GS840E18/32/362.032/2000G; 840E18_r1_04 | Content | • Updated pin description table |
| 840E18_r1_04; 840E18_r1_05 | Content | • Updated BGA pin description table to meet JEDEC standard |
| 840E18A_r1_05; 840E18A_r1_06 | Content/Format | <ul style="list-style-type: none"> • Added “non-A” speed bins to Operating Currents table, AC Electrical Characteristics table, and Ordering Information table • Updated format to fit Technical Documentation standards |
| 840E18A_r1_06; 840E18A_r1_07 | Content/Format | <ul style="list-style-type: none"> • Updated table on page 1 • Updated Operating Currents table on page 18 • Updated Electrical Characteristics table on page 19 • Updated format to comply with present Technical Documentation standards • Corrected typos in revision history table on page 31 |
| 840E18A_r1_07, 840E18A_r1_08 | Content | • Reduced I _{DD} by 20 mA in table on page 1 and Operating Currents table |
| 840E18A_r1_08, 840E18A_r1_09 | Content | • Removed 200 MHz references from entire datasheet |
| 840E18A_r1_09, 840E18A_r1_10 | Content | <ul style="list-style-type: none"> • Updated format • Added 190 MHz speed bin |

4Mb Burst SRAM Revision History

| Rev. Code: Old; New | Types of Changes Format or Content | Page /Revisions;Reason |
|--------------------------------|---|---|
| 840E18A_r1_10, 840E18A_r1_11 | Content | <ul style="list-style-type: none">• Updated entire format• Corrected current numbers to match NBT parts• Removed Preliminary banner |
| 840E18A_r1_11, 840E18A_r1_12 | Content | <ul style="list-style-type: none">• Added Pb-free TQFP information• Added variation number to 119 BGA information |



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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